

# BRMJD44DP

Rev.A Nov.-2023



DATA SHEET

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Silicon 4 6 4transistor in a TO-252 Plastic Package.

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@ f Parameter	... Z Symbol	f › Rating	% y Unit
Collector to Base Voltage	V <sub>CBO</sub>	80	V
Collector to Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter to Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current - Continuous	I <sub>C</sub>	8.0	A
Collector Peak Current	I <sub>CM</sub>	16.0	A
Collector Power Dissipation	P <sub>D</sub> (T <sub>A</sub> =25 - )	1.75	W
Collector Power Dissipation	P <sub>D</sub> (T <sub>C</sub> =25 - )	20	W
Junction Temperature	T <sub>j</sub>	150	
Storage Temperature Range	T <sub>stg</sub>	-55 150	

@ f Parameter	... Z Symbol	y j Ú ^ Test Conditions	Â 4 › Min	Á ° › Typ	Â Ý › Max	% y Unit
Collector to Emitter Breakdown Voltage						
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> = 80V V <sub>BE</sub> = 0				

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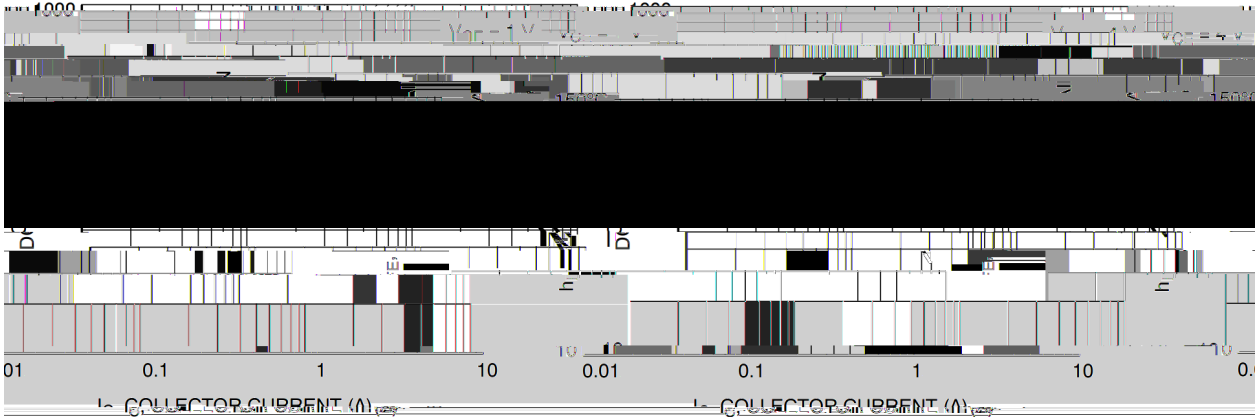
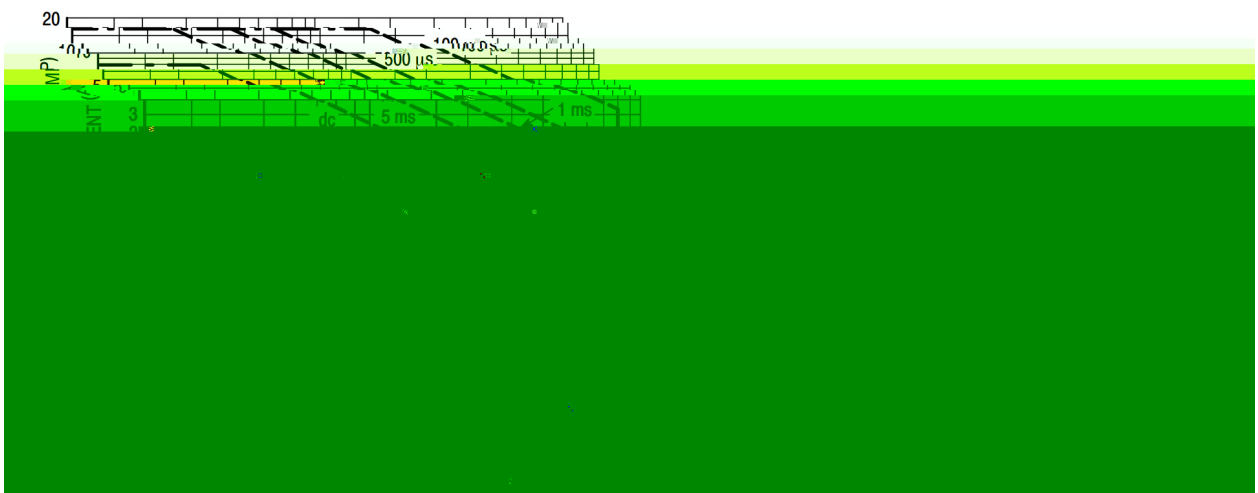
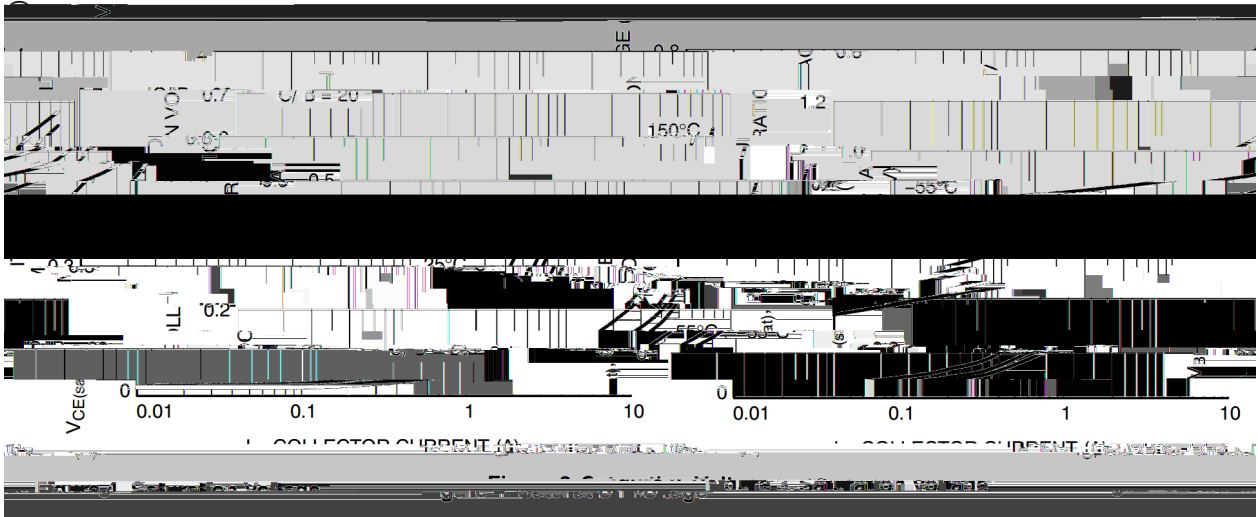
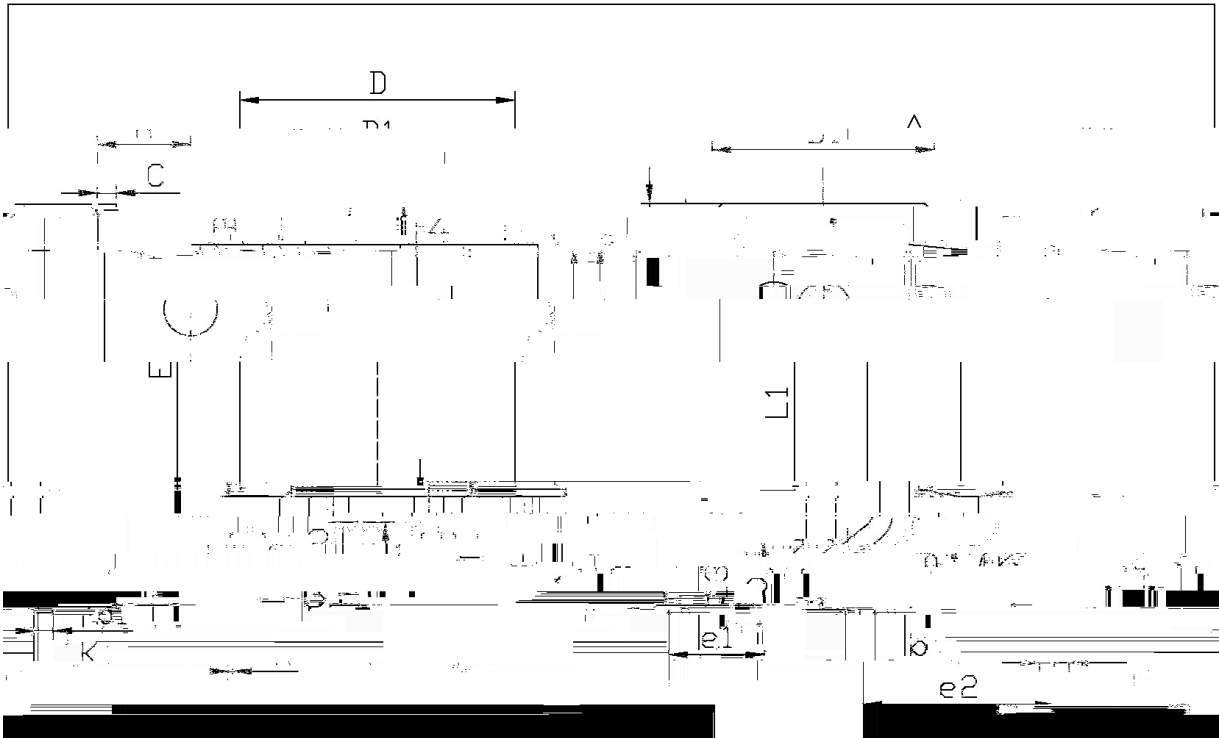


Figure 1. DC Current Gain

Figure 2. DC Current Gain



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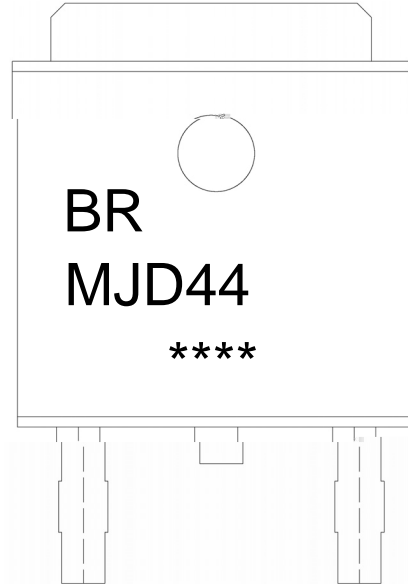


单位: mm

Symbol	Min	Max	Symbol	Min
A	2.20	2.40	F	5.95
B	0.50	0.62	G	4.75
C	0.45	0.55	H	9.45
D	5.16	5.50	I	0.00
E	0.66	0.80	J	0.00
K	0.00	0.00	L	0.00
M	0.00	0.00	N	0.00
O	0.00	0.00	P	0.00
Q	0.00	0.00	R	0.00
S	0.00	0.00	T	0.00
U	0.00	0.00	V	0.00
W	0.00	0.00	X	0.00
Y	0.00	0.00	Z	0.00
e1	0.00	0.00	e2	0.00

12-252

, M y f / M j b



<sup>a</sup> ϕ y  
BR y                   , [ W A  
3 0 \* y               ° Z W A  
                          y               ÿ D Z W A k š ÿ D Z J

Note:  
BR:                   Company Code  
MJD44:             Product Type Code  
\*\*\*\*:                Lot No. Code, code change with Lot No

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